Intrinsic correlated electronic structure of CrO₂ revealed by hard x-ray photoemission spectroscopy

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Bulk-sensitive hard x-ray photoemission spectroscopy (HAXPES) reveals for as-grown epitaxial films of half-metallic ferromagnetic $CrO_2(100)$ a pronounced screening feature in the $Cr 2p_{3/2}$ core level and an asymmetry in the O 1*s* core level. This gives evidence of a finite, metal-type Fermi edge, which is surprisingly not observed in HAXPES. A spectral weight shift in HAXPES to below the Fermi energy is attributed to single-ion recoil effects due to high-energy photoelectrons. In conjunction with inverse PES the intrinsic correlated Mott-Hubbard-type electronic structure is unraveled, yielding an averaged Coulomb correlation energy $U_{av} \cong 3.2$ eV.

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Transition metal oxides are strongly correlated electron systems, which exhibit a wealth of phenomena and potential, a perspective most challenging to modern solid state physics.^{1,2} In the theoretical description of the electronic structure of transition metal oxides seminal progress is owed to dynamical mean-field theory (DMFT).^{3,4} This method has called for intrinsic, bulk-sensitive photoemission spectroscopy (PES).⁵ The reason is obvious: because electronic states of the clean surface differ from those in the bulk due to the increase in U/t, where U is the on-site electron Coulomb repulsion energy and t is the electron hopping energy between lattice sites. Experimentally a breakthrough toward determining the intrinsic bulk electronic structure occurred due to the development of hard xray PES (HAXPES) with a probing depth of 5-10 nm.⁶⁻⁹ In this context a very controversial and provoking case, overdue for examination, is the half-metallic ferromagnet CrO_2 , ^{10,11} which exhibits a metastable surface, transforming into the stable antiferromagnetic insulator Cr2O3.10 For CrO2 a discrepancy exists between the correlated Fermi-liquid-type metallic behavior^{10,12} and the very small intensity of the sputter-cleaned surface in ultraviolet PES (UPES) near the Fermi energy E_F .¹³ The latter was conjectured to be due to surface relaxation of CrO₂(001).¹⁴ The metallicity of CrO₂(100) was even questioned based on UPES measurements.¹⁵ In contrast, an enhanced spectral weight near E_F due to the orbital Kondo effect has been predicted using DMFT.¹⁶ However, the theoretical description of electronic and (magneto-)optical data of CrO₂ has raised doubts about the relevance of strong Hubbard-type correlations.¹⁷⁻²⁰ This controversy and the surface-related problems described above stress the need to employ HAXPES in addition to and in comparison with soft x-ray PES (SXPES).^{8,21,22} Despite the interest in CrO₂ for spintronics applications,^{23,24} because of its high spin polarization,^{13,17,25–28} the intrinsic correlated electronic structure still remains to be unraveled.29

Here we present a bulk-sensitive investigation of valence band states and core levels of CrO_2 by means of HAXPES using photon energies of $h\nu \approx 8$ keV. The photoemission intensity near E_F observed by HAXPES is unexpectedly small, in contrast to the metal-type Fermi edge observed by SXPES. However, with HAXPES we found a strong metallic screening feature in the Cr $2p_{3/2}$ core level and an asymmetry of the O 1s core level, which both imply a finite density of states (DOS) near E_F . This seeming contradiction with the very small photoemission intensity near E_F in HAXPES is resolved by considering single-ion recoil effects in HAXPES. They account for the suppression of the spectral weight near E_F due to its shift to higher binding energy (BE). Using HAXPES, SXPES, and inverse PES (IPES), we identify the salient intrinsic features of the correlated Mott-Hubbard-type electronic structure of CrO₂.

A correlated electronic structure of CrO₂ has been concluded from calculations using the local spin-density approximation LSDA + U.¹⁷ The Cr 3*d* states split in the octahedral crystal field into a lower and an upper state with t_{2g} and e_g symmetry, respectively. The t_{2g} states split further into a strongly localized 3d(xy) orbital near 1 eV BE below E_F and more dispersive $3d(yz \pm zx)$ orbitals. The latter are strongly hybridized with the O 2*p* states, forming bands which cross E_F and cause a self-doping of CrO₂.¹⁷ The exchange splitting shifts the minority-spin states above E_F , giving rise to a spin gap.

The HAXPES and SXPES experiments were performed at 150 or 20 K at the BL19LXU and BL25SU beamlines of SPring-8,³⁰ respectively; we used as-grown, otherwise untreated surfaces of $CrO_2(100)$ epitaxial films. The samples were grown by chemical vapor deposition in an oxygen atmosphere on (100)-oriented TiO₂ substrates.^{23,28,30} To overcome the low photoionization cross section of the Cr 3d and O 2p valence states for $h\nu > 1000$ eV the PES resolution was set to 250 meV (FWHM), while it was set to 100, 60, and 20 meV, respectively, for $h\nu = 700$, 200, and 11.6 eV. To optimize the photoelectron emission, a so-called *p*-polarization configuration was employed for HAXPES, whereas fully circularly polarized light was used for SXPES below hv = 2 keV. The UPES (hv = 11.6 eV) and IPES measurements were performed in laboratory systems, where both the as-grown and sputter-cleaned surfaces were measured.³⁰

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FIG. 1. (Color online) Valence band PES of epitaxial $CrO_2(100)$ films at 20 K for different photon energies in normal emission. The surfaces are as grown, including a nominal Cr_2O_3 surface layer.

Figure 1 shows valence band PES of as-grown $CrO_2(100)$ in normal emission at different photon energies (and varying probing depth δ),³¹ ranging from 11.6 eV ($\delta \leq 1$ nm) to 8180 eV ($\delta \approx 10$ nm). Besides a broad peak near 1.75 eV BE for $hv = 200 \,\text{eV}$, a peak emerges with increasing photon energy near 1.0 eV BE which becomes enhanced for hv = 8180 eV. At lower photon energies (<200 eV) the contribution of the insulating surface Cr₂O₃ layer of roughly 2 nm thickness²⁴ is mostly probed, judging from the low photoemission intensity near E_F (Fig. 1 and Ref. 32). With higher photon energies of 700 eV ($\delta \approx 1.4$ nm) and 1220 eV ($\delta \approx 2.2$ nm) the photoemission spectra show a metal-type Fermi edge. The Fermi edge for hv = 1220 eV is broader than the one for $h\nu = 700$ eV, because of the lower resolution. A metallic Fermi edge was also observed for $h\nu = 385$ eV with 400 meV resolution.³³ However, most unexpectedly we observe no metal-like Fermi edge in HAXPES using hv = 8180 eV, for which bulk properties are expected. Please note that for $E_F \leq E_B \leq 0.2$ eV, where E_B is the binding energy, the very weak intensity increases almost linearly with increasing E_B , showing a steeper slope above 0.2 eV BE.

In Fig. 2 we show the valence band spectrum of CrO_2 for hv = 7942 eV and for $E_F \leq E_B \leq 3$ eV at 20 and 150 K together with the Fermi edge of Au. Besides the prominent peak at 1.0 eV BE a shoulder near 2.1 eV BE is identified. Please note that there is no significant temperature dependence in the spectra in Fig. 2. The photoemission intensity for 20 K near E_F is expanded by a factor of 5, differing strongly from that of Au. It evidences the absence of a metallic Fermi edge of CrO₂ in HAXPES. The features of Fig. 2 and its overview for $E_F \leq E_B \leq 14$ eV (Ref. 30) will be discussed below.

The HAXPES core level spectra help to resolve the puzzle about the intrinsic metallicity of CrO_2 . The O 1s core level in Fig. 3(a) for hv = 1490 eV exhibits satellites at 2 and 4 eV BE above its maximum at 528 eV, which are strongly reduced for hv = 7942 and 8180 eV. These satellites are due to O 2 p-O 2p charge transfer and result most likely from a surface-induced



FIG. 2. (Color online) Valence band PES of epitaxial $CrO_2(100)$ films for $h\nu = 7942$ eV in normal emission at 150 and 20 K. The red and blue lines are guides to the eye. Near E_F the CrO_2 spectrum at 20 K (expanded five times) is compared to that of a Au film.

chemical shift of the O 1*s* core level of Cr₂O₃ and from surfaceadsorbed oxygen.³⁰ Most pronounced is the asymmetry in the line shape of the O 1*s* core level at 528 eV BE in the latter two HAXPES spectra. This asymmetry reflects the intrinsic finite DOS of unoccupied states near E_F ,^{34,35} implying also a nonzero O 2*p* and Cr 3*d* partial DOS of occupied states at E_F . The weak peaks in the HAXPES spectra near 9 and 11 eV BE above the O 1*s* peak are due to Cr $3d(e_g)$ –O 2*p* charge transfer satellites, analogous to the case of cuprates.³⁵ The broad feature in Fig. 3(a) near 29 eV BE above the O 1*s* peak is attributed to plasmon excitations.

Another conclusive feature is found for the Cr $2p_{3/2}$ core level at 576 eV BE in Fig. 3(b). For hv = 1490 eV the Cr $2p_{3/2}$ level exhibits a weak shoulder near 575 eV BE, which develops for $h\nu \approx 8$ keV into a small but sharp peak. This sharp peak at 575 eV BE is obviously a bulk feature and is attributed to a well-screened satellite.^{8,34} The metallic screening of the 2p core-hole potential in the PES final state is due to charge transfer from valence band states at E_F . Such a well-screened satellite was identified by HAXPES for the Mn $2p_{3/2}$ level in the metallic regime of $La_{1-x}Sr_xMnO_3$.⁸ This screening due to hybridized Mn 3d and doping-induced states near E_F of metallic $La_{1-x}Sr_xMnO_3$ has to be replaced in the case of CrO_2 by the 2p-3d hybridized states near E_F . The latter states account for the well-screened feature of the $2p_{3/2}$ level of CrO₂, supporting its intrinsic metallicity for one spin channel. The Cr $2p_{1/2}$ level positioned at 586 eV BE does not exhibit such a satellite, most likely due to multiple configurational interactions and lifetime effects.³⁰

In order to reconcile the discrepancy in HAXPES between the well-screened $2p_{3/2}$ core level evidencing metallicity and the very small photoemission intensity near E_F , we attribute the latter observation to recoil effects,³⁶ i.e., to a shift of orbital-dependent spectral weight to a BE higher than E_F . These recoil effects induced by the emission of high-energy photoelectrons in HAXPES are relevant upon photoexciting not only core levels but also valence band states of light



FIG. 3. (Color online) PES of epitaxial CrO₂(100) films at 20 K for different photon energies. (a) O 1*s* core level PES; expanded ten times for $h\nu = 8180$ eV. (b) Cr 2*p* core level PES; the Cr 2*p*_{3/2} state near 576 eV BE exhibits a well-screened feature near 575 eV.

elements.³⁷ Instead of the whole crystal, the single ion is found to accept the photoelectron momentum. The single-ion recoil shift is given by $E_R \sim E_K(m/M) \sim (h\nu - E_B)(m/M)$, where E_K is the photoelectron kinetic energy, *m* the electron mass, and M the nuclear mass. Estimates of the single-ion recoil shifts show that, e.g., the O 1s core level of CrO_2 near 528 eV BE is shifted towards larger BE with respect to E_F by $E_R^H \approx 260$ meV in HAXPES ($h\nu = 8180$ eV) compared to $E_R^S \approx 24$ meV in SXPES ($h\nu = 1220$ eV). The difference between the two types of spectra amounts to $E_R^{H-S}(O \ 1s) = 236$ meV. For the Cr $2p_{3/2}$ core level near 576 eV BE the recoil shift is estimated as $E_R^H \approx 81 \text{ meV}$ compared to $E_R^S \approx 7$ meV, thus yielding $E_R^{H-S}(\text{Cr } 2p_{3/2}) =$ 74 meV. Consequently, the splitting between O 1s and Cr $2p_{3/2}$ states is estimated as $E_R^{H-S}(\text{O} 1s) - E_R^{H-S}(\text{Cr } 2p_{3/2}) =$ 236 meV - 74 meV = 162 meV smaller in HAXPES compared to SXPES. In our experiment, the O 1s and Cr $2p_{3/2}$ core levels measured each for hv = 7942 eV with reference



FIG. 4. (Color online) IPES spectra at room temperature on as-grown and sputter-cleaned [using Ne⁺ ions (Ref. 30)] epitaxial $CrO_2(100)$ films.

to $h\nu = 1490$ eV (see the Supplemental Material³⁰ Fig. 4) show (H-S) shifts of 180 and 70 meV, respectively, which compare reasonably well with the corresponding estimates of 219 and 68 meV. Hence, the experimental splitting of $E_R^{H-S}(O \ 1s) - E_R^{H-S}(Cr \ 2p_{3/2}) = 180 - 70 = 110 \text{ meV}$ is in fair agreement with the estimate of 219 - 68 = 151 meV, given the crude single-ion recoil approximation. On the other hand, concerning the 2p-3d hybridized valence band states of CrO₂, which show experimentally a wide spread in energy and no specific line shape, the recoil shifts cannot be determined straightforwardly. Hence an upper estimate of the recoil shifts between HAXPES ($h\nu = 8180 \text{ eV}$) and SXPES $(h\nu = 1220 \text{ eV})$ of the O 2p and Cr 3d states is obtained by comparison with the above O 1s and Cr 2p states, amounting at most to $E_R^{H-S}(O\ 2p) - E_R^{H-S}(Cr\ 3d) \approx 162$ meV. Because of the experimental resolution, only a *p* vs *d* states weighted average of the two recoil shifts can be observed, which is estimated by these numbers to be at least 135 meV.³⁰ This shift value agrees roughly with the energy range $E_F \leq E_B \leq$ 0.2 eV in the HAXPES spectrum ($h\nu = 8180$ eV, Fig. 1) over which the intensity is increasingly suppressed toward smaller BE. This gradual suppression toward E_F instead of a rigid shift is attributed to nonideal single-nucleus recoil due to slight collisions with neighboring atoms. Please note that despite the 250 meV HAXPES resolution, a recoil shift of, e.g., 100 meV can still be resolved.³⁰ Moreover, the strongly suppressed intensity of the *p*-*d* hybridized states for $E_F \leq E_B \leq$ 0.2 eV in HAXPES compared to SXPES (Fig. 1) is not due to a more strongly decreasing photoionization cross section of the O 2p atomic subshell with increasing hv compared to the Cr 3d subshell.³⁰

We now discuss the electronic structure of CrO_2 in terms of the Mott-Hubbard model.^{3,4,29,34} Based on the above discussion we attribute the peak in Fig. 2 near 1 eV BE below E_F to the (coherent) quasiparticle peak of *p*-*d* hybridized states and the weak (incoherent) peak near 2.1 eV to the lower Hubbard band (LHB). The latter feature appeared similarly in UPES after prolonged surface sputtering.²⁸ The weak intensity near 2.1 eV in Fig. 2 is most likely due to the strong *p*-*d* hybridization. A similarly weak photoemission intensity has been found for the LHB of strongly correlated Sr₂RuO₄.³⁸ On the other hand, the upper Hubbard band (UHB) is identified by IPES.³⁹ In this experiment, the emitted photon energy is 9.9 eV and the overall energy resolution is 350 meV.⁴⁰ After sputtering the as-grown film surface, the structureless background intensity in Fig. 4 changes into a broad maximum around about -2.8 eV BE above E_F , which we attribute to the UHB. A small but finite intensity appears near E_F , consistent with UPES ($h\nu = 11.6 \text{ eV}$) after identical sputtering (see the Supplemental Material³⁰ Fig. 1). A peak near -3.6 eVBE above E_F has been found in bremsstrahlung isochromat spectroscopy.⁴¹ The measurements, however, were carried out on compressed CrO₂ powder samples, which were scraped in situ. By the energy difference between the LHB near 2.1 eV and the UHB at |-2.8 eV| we obtain an estimate of the local (intraorbital) Coulomb repulsion U of about 4.9 \pm 0.2 eV. From this value we have to subtract the d-d exchange splitting of 1.7 eV obtained from the LSDA calculation,²⁵ which neglects correlation effects. Hence, we obtain for the averaged d-d Coulomb interaction⁵ $U_{av} \cong 4.9$ $-1.7 \cong 3.2$ eV. A value of the *d-d* Coulomb interaction U = 3.0 eV has been used in electronic structure calculations due to the constrained screening method.¹⁷

In analogy to the screening of the Cr $2p_{3/2}$ core level it may be suggestive to consider the Kondo screening of a localized *d* moment by the Cr 3d–O 2p hybridized states. Craco *et al.*¹⁶ tested the scenario of an orbital Kondo effect within LDA + *U* and DMFT calculations. As impurity solver the iterated perturbation theory (IPT) approximation was used. A pronounced quasicoherent spectral weight is predicted at E_F . It disagrees, however, with the experimentally observed

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photoemission intensity near E_F for photon energies ranging from 11.6 to 8180 eV and for temperatures between 300 and 20 K (Figs. 1 and 2 here and Figs. 1 and 2 in the Supplemental Material³⁰).

In conclusion, the comparison of core level and valence state shifts of CrO₂ in HAXPES and SXPES reveals the crucial role of single-ion recoil effects in HAXPES. They result for the *p*-*d* hybridized valence band states in a significant shift (>100 meV) of spectral weight toward higher BE below E_F . CrO₂ appears as a favorable recoil-effect case because of its less dense, open rutile structure, where about 66% of the unit cell volume lies outside the atomic spheres.²⁵ Despite the small HAXPES intensity near E_F , the asymmetry of the O 1s core level and the bulk-type screening feature in the Cr $2p_{3/2}$ level corroborate the metallicity of CrO₂ and its intrinsic nonvanishing, finite DOS near E_F . This is also supported by our IPES (Fig. 4) and UPES (Fig. 1 in the Supplemental Material³⁰) measurements for the sputter-cleaned samples. Along this line we do not find evidence for an anomaly near E_F due to a predicted orbital Kondo effect. By employing HAXPES and IPES, the intrinsic correlated Mott-Hubbardtype electronic structure is identified unambiguously. For this there remains still room for a deeper understanding by applying the DMFT approach.²⁹

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